

isc Silicon NPN Power Transistor

BD245/A/B/C

DESCRIPTION

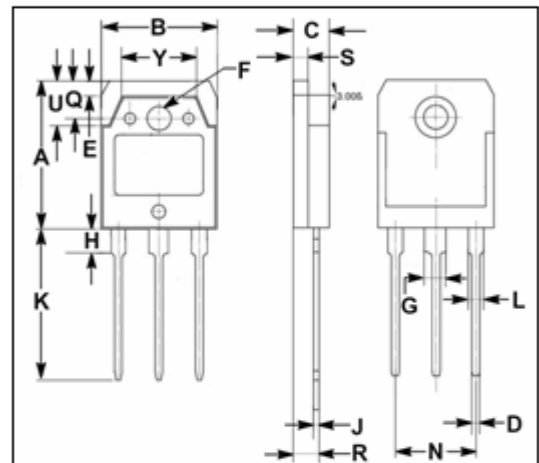
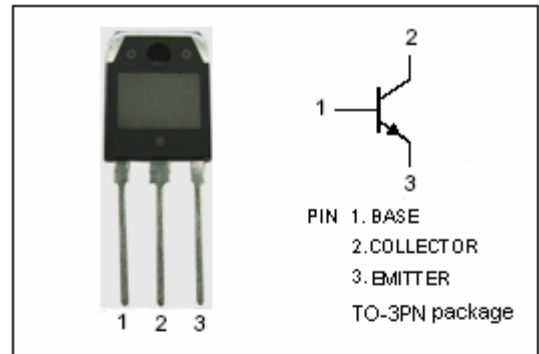
- Collector Current $-I_C = 10A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 45V(\text{Min})$ - BD245; $60V(\text{Min})$ - BD245A
 $80V(\text{Min})$ - BD245B; $100V(\text{Min})$ - BD245C
- Complement to Type BD246/A/B/C

APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 100\Omega$)	BD245	55	V
		BD245A	70	
		BD245B	90	
		BD245C	115	
V_{CEO}	Collector-Emitter Voltage	BD245	45	V
		BD245A	60	
		BD245B	80	
		BD245C	100	
V_{EBO}	Emitter-Base Voltage	5	V	
I_C	Collector Current-Continuous	10	A	
I_{CM}	Collector Current-Peak	15	A	
I_B	Base Current	3	A	
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	W	
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80		
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C}/\text{W}$

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BD245	$I_C=30\text{mA}; I_B=0$	45			V
		BD245A		60			
		BD245B		80			
		BD245C		100			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C=3\text{A}; I_B=0.3\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C=10\text{A}; I_B=2.5\text{A}$			4.0	V
$V_{BE(on)-1}$	Base-Emitter On Voltage		$I_C=3\text{A}; V_{CE}=4\text{V}$			1.6	V
$V_{BE(on)-2}$	Base-Emitter On Voltage		$I_C=10\text{A}; V_{CE}=4\text{V}$			3.0	V
I_{CES}	Collector Cutoff Current	BD245	$V_{CE}=55\text{V}; V_{BE}=0$			0.4	mA
		BD245A	$V_{CE}=70\text{V}; V_{BE}=0$				
		BD245B	$V_{CE}=90\text{V}; V_{BE}=0$				
		BD245C	$V_{CE}=115\text{V}; V_{BE}=0$				
I_{CEO}	Collector Cutoff Current	BD245/A	$V_{CE}=30\text{V}; I_B=0$			0.7	mA
		BD245B/C	$V_{CE}=60\text{V}; I_B=0$				
I_{EBO}	Emitter Cutoff Current		$V_{EB}=5\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain		$I_C=1\text{A}; V_{CE}=4\text{V}$	40			
h_{FE-2}	DC Current Gain		$I_C=3\text{A}; V_{CE}=4\text{V}$	20			
h_{FE-3}	DC Current Gain		$I_C=10\text{A}; V_{CE}=4\text{V}$	4			
f_T	Current-Gain—Bandwidth Product		$I_C=0.5\text{A}; V_{CE}=10\text{V}; f_{\text{test}}=1.0\text{MHz}$	3.0			MHz

Switching times

t_{on}	Turn-on Time	$I_C=1\text{A}; I_{B1}=-I_{B2}=0.1\text{A}; R_L=20\Omega; V_{BE(OFF)}=-3.7\text{V}$		0.2		μs
t_{off}	Turn-off Time			0.8		μs

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